

FINAL PROGRAMME

30th INTERNATIONAL CONFERENCE ON MICROELECTRONICS

Niš, Serbia
October 9th-11th, 2017



organized by
IEEE Serbia and Montenegro Section - ED/SSC Chapter



in cooperation with



Serbian Academy of Science and Arts - Branch in Niš
Faculty of Electronic Engineering, University of Niš



under the co-sponsorship of
IEEE Electron Devices Society



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MINI-COLLOQUIUM ON NANOELECTRONICS

Monday, October 9th

UNIVERSITY OF NIŠ, Univerzitetski trg 2, Niš

- 12:00 **Registration**
- 13:45 **Introductory Remarks and Opening Address**
Ninoslav Stojadinović, University of Niš, Serbia
Chairmen: Marko Topič, University of Ljubljana, Slovenia
Tomislav Šuligoj, University of Zagreb, Croatia
- 14:00 **More Moore, More than Moore, 3D Integration and Diversifications**
Simon Deleonibus, CEA/LETI, France
- 14:30 **Silicon Nanodevices for Intelligent Communications**
Shunri Oda, Tokyo Institute of Technology, Japan
- 15:00 **Silicon in the Nanoscale and the Scaling Issues of Nanowire MOS Transistors**
Hei Wong, City University of Hong Kong, Hong Kong
- 15:30 **Coffee Break**
Chairmen: Simon Deleonibus, CEA/LETI, France
Shunri Oda, Tokyo Institute of Technology, Japan
- 16:00 **Non-Volatility by Spin in Modern Nanoelectronics**
Siegfried Selberherr, Technical University Wien, Austria
- 16:30 **Photovoltaics as Macroelectronics Applying Nanostructures as Nanoelectronics**
Marko Topič, University of Ljubljana, Slovenia
- 17:00 **Innovative Bipolar-CMOS Integration for RF Communication Circuits with Low-Cost High-Performance Horizontal Current Bipolar Transistor (HCBT)**
Tomislav Suligoj, University of Zagreb, Croatia

CONFERENCE PROGRAMME

Monday, October 9th

UNIVERSITY OF NIŠ, Univerzitetski trg 2, Niš

- 18:00 **Conference Opening**
Chairmen: N. Stojadinović, University of Niš, Serbia
S. Deleonibus, CEA/LETI, France
S. Dimitrijević, Griffith University, Nathan, Australia
S. Oda, Tokyo Institute of Technology, Japan
H. Wong, City University of Hong Kong, Hong Kong
- 18:30 **Welcome Cocktail**

CONFERENCE PROGRAMME

Tuesday, October 10th

FACULTY OF ELECTRONIC ENGINEERING, Aleksandra Medvedeva 14, Niš

SESSION: DEVICE PHYSICS, TECHNOLOGY AND TESTING

Room A

Chairmen: A. Paskaleva, Bulgarian Academy of Sciences, Sofia, Bulgaria
S. Dimitrijević, Griffith University, Nathan, Australia

- 9:00 **Nanoelectronic Graphene Devices**
P. I. Hagouel, I.G. Karafyllidis
Optelec, Thessaloniki, Greece
Democritus University of Thrace, Xanthi, Greece
- 9:15 **Functional Role of Ca²⁺ Currents within the Stereocilia as Bio-MEMS: A Modeling Study**
D.L. Sekulic, M.V. Sataric, A.V. Joza
University of Novi Sad, Serbia
- 9:30 **Memristor state transition in reconfigurable microwave filter**
I. Marković, M. Potrebić, D. Tošić
University of Belgrade, Serbia
- 9:45 **Formation of Short Terahertz Electromagnetic Pulses in Nonlinear Paraelectrics**
V. Grimalsky, S. Koshevaya, J. Escobedo-Alatorre, E. Jatirian-Foltides
Autonomous University of State Morelos, Cuernavaca, Mexico
- 10:00 **Simulation of Solo GaN IGBTs**
S. Faramehr, P. Igić
Swansea University, United Kingdom
- 10:15 **A Case Study of C-V Hysteresis Instability in Metal-High-k-Oxide-Silicon Devices with ZrO₂/Al₂O₃/Zr₂O₂ Stack as a Charge Trapping Layer**
A. Skeparovski, D. Spassov¹, A. Paskaleva¹, N. Novkovski
"Ss. Cyril and Methodius" University, Skopje, Macedonia
¹Bulgarian Academy of Sciences, Sofia, Bulgaria
- 10:30 **A Comparison of the Tri-Layer Transmission Line Model and a Finite Element Model for Ohmic Contact Analysis**
F. Algahtani, S. Luong, Y. Pan, M.S. Alnassar, A. Holland
RMIT University, Melbourne, Australia
- 10:45 **SOI Based Double Source Tunnel FET (DS-TFET) with High On-Current and reduced Turn-on Voltage**
N. Bagga, A. Kumar and S. Dasgupta
Indian Institute of Technology Roorkee, India
- 11:00 **Coffee Break**

Chairmen: Z. Stamenkovic, IHP, Frankfurt (Oder), Germany
D. Osipov, University of Bremen, Germany

- 11:30 **Implementation of Fuzzy Logic Operators as Digital Asynchronous Circuits in CMOS Technology**
T. Talaška
UTP University of Science and Technology, Bydgoszcz, Poland
- 11:45 **Parallel Matrix Multiplication in 2-gain Kalman Filter Realized in Hardware**
I. Zbierska¹, T. Talaška², R. Długosz^{1,2}
¹Delphi Poland, Krakow, Poland
²UTP University of Science and Technology, Bydgoszcz, Poland
- 12:00 **Energy-Efficiency vs. Performance Optimization in Low-Power Wireless Transmission**
N. Zogović
Institute Mihajlo Pupin, University of Belgrade, Serbia
- 12:15 **Analog ASIC TID Behavior in a Temperature Range**
A.Y. Borisov, L.N. Kessarinskiy, M.M. Vanzha, M.P. Belova, Y.M. Moskovskaya, D.V. Boychenko, A.Y. Nikiforov, V.V. Enns¹
National Research Nuclear University "MEPhI", Moscow, Russia
¹Design center "SOYUZ", Zelenograd, Moscow, Russia
- 12:30 **Integrated Current Sensor for Automotive Power Switches**
R. Brata, A. Danchiv¹, L. Dobrescu, D. Dobrescu
"Politehnica" University of Bucharest, Romania
¹Infineon Technology Romania, Bucharest, Romania
- 12:45 **Plastic Encapsulated ICs Bonding Reliability Risk Assessment at HT Automotive Application**
M. Blyzniuk, A. Devos¹, M. Furman
Branch Establishment "Melexis-Ukraine", Kyiv, Ukraine
¹Melexis NV, Sint Krispijnstraat, Ieper, Belgium
- 13:15 **Lunch** **Restaurant**

Chairmen: H. Wong, City University of Hong Kong, Kowloon, Hong Kong
A. Napieralski, Lodz University of Technology, Poland

14:30 **SiC Power MOSFETs: The Current Status and the Potential for Future Development**

S. Dimitrijević
Griffith University, Nathan, Australia

15:00 **An Overview of the Modeling and Simulation of the Single Event Transients at the Circuit Level**

M. Andjelkovic, A. Ilic, Z. Stamenkovic, M. Krstic, R. Kraemer
IHP, Frankfurt (Oder), Germany

15:30 **Basic Trends in Electronic Components Product Range Development: Radiation Hardness Aspects**

A.Y. Nikiforov, D.V. Boychenko, V.A. Telets, A.A. Smolin, V.V. Elesin,
A.V. Ulanova, L.N. Kessarinskiy
National Research Nuclear University "MEPhI", Moscow, Russia

16:00 **Coffee Break**

16:30-17:30 **POSTERS 1**

SESSION: DEVICE PHYSICS, TECHNOLOGY AND TESTING

Lobby

Chairmen: P. Igić, Swansea University, United Kingdom
D. Vasiljević Radović, University of Belgrade, Serbia

A1 **Tailorable Effective Optical Response of Dual-metal Plasmonic Crystals**

M. Obradov, J. Lamovec, I. Mladenović, Z. Jakšić¹, S. Vuković,
G. Isić, D. Tanasković
University of Belgrade, Serbia
¹IHTM-CMTM, Serbia

A2 **Stochastic Time Response of Adsorption-Based Micro/Nanobiosensors with a Fluidic Reaction Chamber: the Influence of Mass Transfer**

I. Jokić, Z. Djurić¹, K. Radulović, M. Frantlović
University of Belgrade, Serbia
¹Serbian Academy of Sciences and Arts, Belgrade, Serbia

A3 **Effect of High Energy Ball Milling on the Morphology and Magnetic Properties of Powder Prepared from HD Nd₂Fe₁₄B Material**

V. Jović, J. Lamovec, D. Sojer, D. Lončarević, I. Mladenović,
D. Vasiljević Radović
University of Belgrade, Serbia

- A4 **Characterization of Yttrium Orthoferrite (YFeO₃) Nanoparticles as Humidity Sensor Materials at Room Temperature**
D.L. Sekulic, Z. Lazarevic¹, C. Jovalekic¹, N. Romcevic¹
University of Novi Sad, Serbia
¹University of Belgrade, Serbia
- A5 **On the Design of Compact Intelligent Industrial Transmitters Based on Piezoresistive MEMS Pressure Sensors**
M. Frantlović, P. Poljak, I. Jokić, D. Randjelović, D. Vasiljević Radović
University of Belgrade, Serbia
- A6 **Electrical and Charge Trapping Properties of HfO₂/Al₂O₃ Multilayer Dielectric Stacks**
V. Davidović¹, A. Paskaleva², D. Spassov², E. Guziewicz³, T. Krajewski³, S. Golubović¹, S. Djorić-Veljković¹, I. Manić¹, D. Danković¹, N. Stojadinović^{1,4}
¹University of Niš, Serbia
²Bulgarian Academy of Sciences, Sofia, Bulgaria
³Polish Academy of Sciences, Warsaw, Poland
⁴Serbian Academy of Sciences and Arts, Belgrade, Serbia
- A7 **Modelling of Threshold Voltage Shift in Pulsed NBT Stressed P-Channel Power VDMOSFETs**
D. Danković, I. Manić, N. Stojadinović¹, Z. Prijić, S. Djorić-Veljković, V. Davidović, A. Prijić, A. Paskaleva², D. Spassov², S. Golubović
University of Niš, Serbia
¹Serbian Academy of Sciences and Arts, Belgrade, Serbia
²Bulgarian Academy of Sciences, Sofia, Bulgaria
- A8 **GaN HEMT Small-Signal Modelling: Neural Networks versus Equivalent Circuit**
Z. Marinković, G. Crupi¹, A. Caddemi¹, V. Marković
University of Niš, Serbia
¹University of Messina, Italy
- A9 **Compact Thermal Modelling of Power LED Light Sources**
T. Torzewicz, K. Baran¹, T. Raszkowski, A. Samson, H. Wachta¹, A. Napieralski
Lodz University of Technology, Poland
¹Rzeszow University of Technology, Poland
- A10 **Estimation Technique for LED Sensitivity to Structural Damage based on Minority Carriers Lifetime Measurements**
R.K. Mozhaev, M.E. Cherniak, A.V. Ulanova, A.Y. Nikiforov
National Research Nuclear University "MEPhI", Moscow, Russia
- A11 **Power MOSFET Single Event Burnout Hardness Increasing by Neutron Preirradiation**
L. Kessarinskiy, D. Boychenko, A. Nikiforov, A. Polokhov¹, T. Kritskaya¹, G. Davydov
National Research Nuclear University "MEPhI", Moscow, Russia
¹JSC "Angstrom", Zelenograd, Moscow, Russia
- A12 **Temperature Influence on the TID effects in RadFETs**
V. Felitsyn, B. Podlepetsky, A. Bakerenkov, A. Rodin, Yu. Sukhoroslova
National Research Nuclear University "MEPhI", Moscow, Russia
- A13 **Joint Model of Dose Rate Radiation Effects in Bipolar Devices**
V. Pershenkov, A. Bakerenkov, V. Telets, V. Belyakov, V. Shurenkov, V. Felitsyn, A. Rodin
National Research Nuclear University "MEPhI", Moscow, Russia

- A14 **Numerical Computation of the Physical Shielding Factor for Different Structures of MOSFET in Gamma Irradiation Field**
S. Stanković, R. Ilić, A. Jakšić¹, D. Nikolić, N. Kržanović
University of Belgrade, Serbia
¹University College Cork, Ireland
- A15 **Influence of High Voltage Pulse Trimming on Thick-Film Resistor Quality Indicators**
I. Stanimirović, Z. Stanimirović
Institute for Telecommunications and Electronics IRITEL, Belgrade, Serbia
- A16 **Electrical Properties of Rare Earth Doped BaTiO₃ Ceramics**
V. Paunović, V. Mitić, M. Đorđević, Z. Prijić
University of Niš, Serbia
- A17 **Evaluation of the Mechanical and Tribological Properties of Multilayer CrN/TiN Films Deposited at Low Temperatures**
L. Kolaklieva, S. Rabadzhiyska, R. Kakanakov, V. Chitanov, T. Cholakova, V. Rupetchov¹, G. Mishev¹
Bulgarian Academy of Sciences, Plovdiv, Bulgaria
¹Paisii Hilendarski University Plovdiv, Bulgaria
- A18 **Analysis of Low-pressure DC Breakdown in Air**
E. Živanović
University of Niš, Serbia
- A19 **Capacitance Model for MOSFET Operated in all Regions**
A. Benfdila, A. Lakhlef
University M. Mammeri, Tizi-Ouzou, Algeria
- A20 **Investigation on Cylindrical Gate-All-Around (GAA) Tunnel FETS Scaling**
M. Kessi, A. Benfdila, A. Lakhlef
University M. Mammeri, Tizi-Ouzou, Algeria
- 18:00 **Departure for Gala Dinner**
Faculty of Electronic Engineering
- Gala Diner - Wine Cellar Malcha**

Wednesday, October 11th

FACULTY OF ELECTRONIC ENGINEERING, Aleksandra Medvedeva 14, Niš

SESSION: **SYSTEM DESIGN AND TESTING**

Room A

Chairmen: V. Milovanovic, University of Kragujevac, Serbia
R. Dlugosz, Delphi Poland, Krakow, Poland

- 9:00 **An HDL Model of a Digitally Controlled Oscillator for Rapid Digital PLL Prototyping**
V. Milovanovic, B. Nikolic¹
University of Kragujevac, Serbia
¹University of California at Berkeley, USA
- 9:15 **Low Power SAR ADC with Two-Step Switching Scheme in 65 nm Standard CMOS Process**
D. Osipov, St. Paul
University of Bremen, Germany
- 9:30 **The Implementation of Harmonic Analysis Methods in Active Power Filters Control**
B. Jovanović, P. Petković, S. Milenković
University of Niš, Serbia
- 9:45 **Comparison of the SET Sensitivity of Standard Logic Gates Designed in 130 nm CMOS Technology**
M. Andjelkovic, M. Krstic, R. Kraemer
IHP, Frankfurt (Oder), Germany
- 10:00 **Classification of Nonlinear Loads Based on Artificial Neural Networks**
M. Andrejević Stošović, D. Stevanović¹, M. Dimitrijević
University of Niš, Serbia
¹Innovation Centre of Advanced Technologies (ICAT), Niš, Serbia
- 10:15 **32-channel Self-triggered ASIC for GEM Detectors**
E. Atkin, I. Bulbakov, V. Ivanov¹, P. Ivanov, E. Malankin, D. Normanov, S. Petrovskiy, V. Shumikhin, A. Voronin, V. Samsonov¹
National Research Nuclear University "MEPhI", Moscow, Russia
¹National Research Centre Kurchatov Institute, Gatchina, Russia
- 10:30 **Coffee Break**

SESSION PLENARY SESSION 2**Room A**

Chairmen: A.Y. Nikiforov, NRNU "MEPhI", Moscow, Russia
M. Janicki, Lodz University of Technology, Poland

- 11:00 **Energy and Variability Efficient (EVE) Era is Ahead of Us**
S. Deleonibus
CEA/LETI, France
- 11:30 **The Scaling Issues of Subnanometer EOT Gate Dielectrics for the Ultimate Nano CMOS Technology**
J. Zhang, H. Wong, V. Filip
University of Hong Kong, Kowloon, Hong Kong
University of Bucharest, Magurele, Romania
- 12:00 **High Sensitivity Magnetic Sensors Compatible with Bulk Silicon and SOI IC Technology**
P. Igić, O. Kryvchenkova, S. Farammehr, S. Batcup, N. Janković¹
Swansea University, United Kingdom
¹University of Niš, Serbia
- 12:45 **Lunch** **Restaurant**

14:00-15.00 **POSTERS 2**

SESSION: CIRCUIT DESIGN AND TESTING**Lobby**

Chairmen: T. Talaška, UTP University of Science and Technology, Poland
M. Andrejević Stošović, University of Niš, Serbia

- B1 **Real-time Locating Systems for Smart City and Intelligent Transportation Applications**
M. Banach, R. Dlugosz¹
Poznan University of Technology, Poland
¹Delphi Poland, Krakow, Poland
- B2 **Selected Aspects and Tradeoffs in Transistor Level Implementation of Genetic Algorithms**
S. Jezewski, R. Dlugosz¹
Institute of Informatics, College of Socialand Media Culture, Torun, Poland
¹Delphi Poland, Krakow, Poland
- B3 **Advanced Stand for Transient Thermal Measurements**
T. Torzewicz, A. Sobczak, M. Janicki, A. Napieralski
Lodz University of Technology, Poland

- B4 **A Low-Latency Medium Access Control Protocol for Industrial Wireless LAN Applications**
N. Odhah, K. Tittelbach-Helmrich, Z. Stamenković
IHP, Frankfurt (Oder), Germany
- B5 **The Prediction for Single Event Latchup Sensitivity Parameters of Digital CMOS ICs Based on its Technological Features**
A.E. Rudenkov, A.O. Akhmetov, D.V. Bobrovsky, A.I. Chumakov, A.V. Yanenko, V.M. Uzhegov¹
National Research Nuclear University "MEPhI", Moscow, Russia
¹TSNIIMASH, Korolev, Russia
- B6 **Comparison of On-Chip ADC Testing Techniques**
A.Yu. Egorov, I.A. Mozhaev, P.V. Nekrasov, D.V. Boychenko, I.O. Loskutov
National Research Nuclear University "MEPhI", Moscow, Russia
- B7 **SEFI Cross-section Evaluation by Fault Injection Software Approach and Hardware Detection**
I.O. Loskutov, P.V. Nekrasov, I.I. Shvetsov-Shilovskiy, D.V. Boychenko, V.M. Uzhegov¹
National Research Nuclear University "MEPhI", Moscow, Russia
¹TSNIIMASH, Korolev, Russia
- B8 **FRAM Test Memory Cells Radiation Hardness Research**
I.I. Shvetsov-Shilovskiy, A.B. Boruzdina, A.V. Ulanova, O.M. Orlov¹, Y.A. Matveev, D.V. Negrov
National Research Nuclear University "MEPhI", Moscow, Russia
¹TSNIIMASH, Korolev, Russia
- B9 **Investigation of Ionizing Transients by Femtosecond X-ray Source Ionization**
M.P. Belova, L.N. Kessarinskiy, A.Y. Borisov, A.I. Chumakov, D.V. Boychenko
K.A. Ivanov¹, I.N. Tsybalov¹, R.V. Volkov¹, A.B. Savel'ev¹
National Research Nuclear University "MEPhI", Moscow, Russia
¹M.V. Lomonosov Moscow State University, Moscow, Russia
- B10 **Optimal Laser Wavelengths for Transient Ionizing Response Simulation of CMOS SOI Devices with 0.24 μm Design Rules**
S.B. Shmakov, P.K. Skorobogatov¹, A.V. Ulanova, A.B. Boruzdina¹, G.G. Davydov, A.Y. Nikiforov
Specialized Electronic Systems, Moscow, Russia
¹National Research Nuclear University "MEPhI", Moscow, Russia
- B11 **Total Ionizing Dose Hardness Nondestructive Individual Estimation and Predictive Grading for Silicon-on-insulator ICs**
Y.M. Moskovskaya, G.G. Davydov, A.V. Sogoyan, A.Y. Nikiforov, I.B. Yashanin¹
National Research Nuclear University "MEPhI", Moscow, Russia
¹Scientific Institute of Measurement Systems, N. Novgorod, Russia
- B12 **Total Ionizing Dose Degradation of CMOS 8-transistor Image Sensor with Column ADC**
M. Cherniak, A. Smolin, R. Mozhaev, A. Ulanova, A. Nikiforov
National Research Nuclear University MEPhI, Moscow, Russia

- B13 **Process Parameters Variations Influence on CMOS IC's Hardness to Total Ionizing Dose**
 Y.M. Moskovskaya, A.Y. Nikiforov, D.V. Bobrovskiy, A.V. Ulanova, A.A. Zhukov¹
 National Research Nuclear University "MEPhI", Moscow, Russia
¹SMC «Technological Centre», Zelenograd, Moscow, Russia
- B14 **Battery Capacity Estimation of Wireless Sensor Node**
 G. Nikolić, T. Nikolić, M. Stojčev, B. Petrović, G. Jovanović
 University of Niš, Serbia
- B15 **Analog Device Design for Testability in the Case of Oscillation Based Testing**
 M. Petrović, M. Milić
 University of Niš, Serbia

SESSION: SYSTEM DESIGN AND TESTING

Lobby

Chairmen: M. Stojčev, University of Niš, Serbia
 M. Zogović, Institute Mihajlo Pupin, Serbia

- C1 **Asynchronous Early Output Section-Carry Based Carry Lookahead Adder with Alias Carry Logic**
 P. Balasubramanian, C. Dang, D.L. Maskell, K. Prasad¹
 Nanyang Technological University, Singapore
¹Auckland University of Technology, New Zealand
- C2 **Approximate Ripple Carry and Carry Lookahead Adders – A Comparative Analysis**
 P. Balasubramanian, C. Dang, D.L. Maskell, K. Prasad¹
 Nanyang Technological University, Singapore
¹Auckland University of Technology, New Zealand
- C3 **Dual-Phase-Lag Thermal Model of Test Microchip Structure Dedicated to Electronic Circuit Thermal Properties Estimation using Artificial Intelligence**
 T. Raszkowski, A. Samson, M. Zubert, M. Janicki
 Lodz Technical University, Poland
- C4 **Design and Testing Issues of a High-Speed SOI CMOS Dual-Modulus Prescaler for Radiation Tolerant Frequency Synthesizers**
 D.I. Sotskov, V.V. Elesin, K.M. Amburkin, G.N. Nazarova,
 N.A. Usachev, A.Y. Nikiforov
 National Research Nuclear University "MEPhI", Moscow, Russia
- C5 **Flip-chip ICs SEE Testing Technique**
 D.V. Bobrovsky, A.A. Pechenkin, A.A. Novikov, A.I. Chumakov,
 N.V. Ryasnoy¹, Y.V. Churilin¹
 National Research Nuclear University "MEPhI", Moscow, Russia
¹JSC SRC «Progress», Samara, Russia

- C6 **SPICE-Level Layout-Aware Single Event Effects Simulation of Majority Voters**
A.O. Balbekov¹, M.S. Gorbunov^{1,2}, G.I. Zebrev²
¹Scientific Research Institute of System Analysis, Russian Academy of Sciences, Moscow, Russia
²National Research Nuclear University "MEPhI", Moscow, Russia
- C7 **Compendium of TID Influence on SEE Sensitivity Investigation**
A.A. Novikov, A.A. Pechenkin, A.I. Chumakov, A.N. Tsirkov, M.P. Belova
National Research Nuclear University "MEPhI", Moscow, Russia
- C8 **Frequency Dependence of SEU in 0.18um Processor**
V.A. Marfin, P.V. Nekrasov, I.O. Loskutov, A.Y. Nikiforov
National Research Nuclear University "MEPhI", Moscow, Russia
- C9 **Experiments on Electrical Overstress Influence on Digital ICs Depending on the Input/Output Port Configuration**
A.N. Shemonaev, K.A. Epifantsev, P.K. Skorobogatov
National Research Nuclear University "MEPhI", Moscow, Russia
- C10 **The Specialized Pulse Voltage Generator EMI-0502**
A.N. Shemonaev, K.A. Epifantsev, P.K. Skorobogatov
National Research Nuclear University "MEPhI", Moscow, Russia
- 15:15 **Conference Closing**
Best Paper Awards

30th INTERNATIONAL CONFERENCE ON MICROELECTRONICS

FINAL PROGRAMME

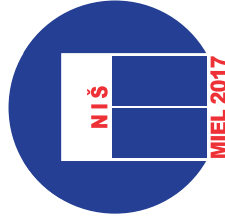
MONDAY, October 9th
UNIVERSITY OF NIŠ
 Univerzitetski trg 2, Niš

12:00
 Registration

13:45
 MINI-COLLOQUIUM
 ON NANO-ELECTRONICS

18:00
 Conference Opening

18:30
 Welcome Cocktail



TUESDAY, October 10th
FACULTY OF ELECTRONIC ENGINEERING
 Aleksandra Medvedeva 14, Niš

9:00
 Room A
 Session:
 DEVICE PHYSICS,
 TECHNOLOGY AND TESTING

11:00
 Coffee Break

11:30
 Room A
 Session:
 CIRCUITS DESIGN
 AND TESTING

13:15
 Restaurant
 Lunch

14:30
 Room A
 PLENARY SESSION 1

16:00
 Coffee Break

16:30
 Lobby
 Posters 1
 Session: DEVICE PHYSICS,
 TECHNOLOGY AND TESTING

17:30
 18:00
 Departure for Gala Dinner

WEDNESDAY, October 11th
FACULTY OF ELECTRONIC ENGINEERING
 Aleksandra Medvedeva 14, Niš

9:00
 Room A
 Session:
 SYSTEM DESIGN
 AND TESTING

10:30
 Coffee Break

11:00
 Room A
 PLENARY SESSION 2

12:45
 Restaurant
 Lunch

14:00
 Lobby
 Posters 2
 Session: CIRCUIT DESIGN
 AND TESTING
 Session: SYSTEM DESIGN
 AND TESTING

15:00
 15:15
 Conference Closing
 Best Paper Awards

IMPORTANT ADDRESS

Prof. Dr. Ninoslav Stojadinović
Conference Chairman

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